This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (original): A method for transferring a device, comprising the steps of:

irradiating, selectively, an interface between a first substrate and a device included on the first substrate with an energy beam and transmitting the energy beam through the first substrate to selectively release the device;

transferring the released device onto a device holding layer included on a device holding substrate; and

transferring the device from the device holding layer onto a second substrate.

Claim 2 (canceled)

Claim 3 (original): A method for transferring a device as claimed in claim 1, further comprising the step of providing an adhesive layer on the second substrate wherein the adhesive layer is irradiated with the energy beam when the device is transferred from the device holding layer onto the second substrate.

Claim 4 (original): A method for transferring a device as claimed in claim 1, wherein the device is formed of a material which produces ablation upon irradiation with the energy beam, and wherein ablation is generated by the selective irradiation with the energy beam to cause exfoliation at an interface between the device and the first substrate.

Claims 5-8 (canceled)

Claim 9 (original): A method for transferring a device as claimed in claim 1, wherein the device is a light-emitting device.

Claim 10 (canceled)

Claim 11 (original): A method for transferring a device as claimed in claim 1, wherein the device holding layer is a silicone resin layer.

Claim 12 (original): A method for producing a device holding substrate, comprising the steps of:

preparing a substrate that includes a device having a pointed head portion;

providing an uncured silicone resin layer on a device holding substrate;

adhering the substrate that includes the device having the pointed head portion to the device holding substrate; and

providing a recessed portion in a surface of the silicone resin layer shaped to fit the pointed head portion.

Claim 13 (canceled)

Claim 14 (original): A device holding substrate, comprising:

a substrate; and

a silicone resin layer provided on the substrate, wherein a surface of the silicone resin layer has a recessed portion shaped to fit a pointed head portion of a device.

Claim 15 (previously presented): A method for transferring a device, comprising the steps of:

irradiating, selectively, an interface between a first substrate and a device having one of a pointed head portion and a flat plate-shaped structure, included on the first substrate with an energy beam and transmitting the energy beam through the first substrate to selectively release the device;

transferring the released device onto a device holding layer included on a device holding substrate; and

transferring the device from the device holding layer onto a second substrate.

Claim 16 (previously presented): A method for transferring a device as claimed in claim 15, further comprising the step of cleaning the device on the device holding layer after the device is transferred onto the device holding layer.

Claim 17 (previously presented): A method for transferring a device as claimed in claim 15, further comprising the step of providing an adhesive layer on the second substrate wherein the adhesive layer is irradiated with the energy beam when the device is transferred from the device holding layer onto the second substrate.

Claim 18 (previously presented): A method for transferring a device as claimed in claim 15, wherein the device is formed of a material which produces ablation upon irradiation with the energy beam, and wherein ablation is generated by the selective irradiation with the energy beam to cause exfoliation at an interface between the device and the first substrate.

Claim 19 (previously presented): A method for transferring a device as claimed in claim 18, wherein the material is a nitride semiconductor material.

Claim 20 (previously presented): A method for transferring a device as claimed in claim 19, wherein the nitride semiconductor material is a GaN-based material.

Claim 21 (previously presented): A method for transferring a device as claimed in claim 15, wherein the first substrate is a sapphire substrate.

Claim 22 (previously presented): A method for transferring a device as claimed in claim 15, wherein the device is a light-emitting device.

Claim 23 (previously presented): A method for transferring a device as claimed in claim 15, wherein the device holding layer includes a surface with a recessed portion shaped to fit the pointed head portion.

Claim 24 (previously presented): A method for transferring a device as claimed in claim 15, wherein the device holding layer is a silicone resin layer.

Claim 25 (previously presented): A method for producing a device holding substrate, comprising the steps of:

preparing a substrate that includes a device having a pointed head portion;

providing an uncured silicone resin layer on a device holding substrate;

coating the device having a pointed head portion with a release agent;

adhering the substrate that includes the device having the pointed head portion to the device holding substrate; and

providing a recessed portion in a surface of the silicone resin layer shaped to fit the pointed head portion.

Claim 26 (previously presented): A method for transferring a device, comprising the steps of:

irradiating, selectively, an interface between a first substrate and a device included on the first substrate with an energy beam to selectively release the device;

transferring the released device onto a device holding layer included on a device holding substrate;

cleaning the device on the device holding layer; and

transferring the device from the device holding layer onto a second substrate.

Claim 27 (previously presented): A method for transferring a device as claimed in claim 26, further comprising the step of providing an adhesive layer on the second substrate wherein the adhesive layer is irradiated with the energy beam when the device is transferred from the device holding layer onto the second substrate.

Claim 28 (previously presented): A method for transferring a device as claimed in claim 26, wherein the device is formed of a material which produces ablation upon irradiation with the energy beam, and wherein ablation is generated by the selective irradiation with the energy beam to cause exfoliation at an interface between the device and the first substrate.

Claim 29 (previously presented): A method for transferring a device as claimed in claim 28, wherein the material is a nitride semiconductor material.

Claim 30 (previously presented): A method for transferring a device as claimed in claim 29, wherein the nitride semiconductor material is a GaN-based material.

Claim 31 (previously presented): A method for transferring a device as claimed in claim 26, wherein the first substrate is a sapphire substrate.

Claim 32 (canceled)

Claim 33 (previously presented): A method for transferring a device as claimed in claim 26, wherein the device is a light-emitting device.

Claim 34 (previously presented): A method for transferring a device as claimed in claim 26, wherein the device has a pointed head portion, and the device holding layer includes a surface with a recessed portion shaped to fit the pointed head portion.

Claim 35 (previously presented): A method for transferring a device as claimed in claim 26, wherein the device holding layer is a silicone resin layer.

Claim 36 (previously presented): A method for transferring a device, comprising the steps of:

irradiating, selectively, an interface between a first substrate and a device having a pointed head portion included on the first substrate with an energy beam and transmitting the energy beam through the first substrate to selectively release the device;

transferring the released device onto a device holding layer included on a device holding substrate, wherein the device holding layer includes a surface with a recessed portion shaped to fit the pointed head portion; and

transferring the device from the device holding layer onto a second substrate.

Claim 37 (previously presented): A method for transferring a device as claimed in claim 36, further comprising the step of cleaning the device on the device holding layer after the device is transferred onto the device holding layer.

Claim 38 (previously presented): A method for transferring a device as claimed in claim 36, further comprising the step of providing an adhesive layer on the second substrate wherein the adhesive layer is irradiated with the energy beam when the device is transferred from the device holding layer onto the second substrate.

Claim 39 (previously presented): A method for transferring a device as claimed in claim 36, wherein the device is formed of a material which produces ablation upon irradiation with the energy beam, and wherein ablation is generated by the selective irradiation with the energy beam to cause exfoliation at an interface between the device and the first substrate.

Claim 40 (previously presented): A method for transferring a device as claimed in claim 39, wherein the material is a nitride semiconductor material.

Claim 41 (previously presented): A method for transferring a device as claimed in claim 40, wherein the nitride semiconductor material is a GaN-based material.

Claim 42 (previously presented): A method for transferring a device as claimed in claim 36, wherein the first substrate is a sapphire substrate.

Claim 43 (previously presented): A method for transferring a device as claimed in claim 36, wherein the device is a light-emitting device.

Claim 44 (previously presented): A method for transferring a device as claimed in claim 36, wherein the device holding layer is a silicone resin layer.

Claim 45 (previously presented): A method for transferring a device, comprising the steps of:

irradiating, selectively, an interface between a first substrate and a device having a pointed head portion and a flat plate-shaped structure included on the first substrate with an energy beam to selectively release the device;

transferring the released device onto a device holding layer included on a device holding substrate;

cleaning the device on the device holding layer; and

transferring the device from the device holding layer onto a second substrate.

Claim 46 (previously presented): A method for transferring a device as claimed in claim 45, further comprising the step of providing an adhesive layer on the second substrate wherein the adhesive layer is irradiated with the energy beam when the device is transferred from the device holding layer onto the second substrate.

Claim 47 (previously presented): A method for transferring a device as claimed in claim 45, wherein the device is formed of a material which produces ablation upon irradiation with the energy beam, and wherein ablation is generated by the selective irradiation with the energy beam to cause exfoliation at an interface between the device and the first substrate.

Claim 48 (previously presented): A method for transferring a device as claimed in claim 47, wherein the material is a nitride semiconductor material.

Claim 49 (previously presented): A method for transferring a device as claimed in claim 48, wherein the nitride semiconductor material is a GaN-based material.

Claim 50 (previously presented): A method for transferring a device as claimed in claim 45, wherein the first substrate is a sapphire substrate.

Claim 51 (previously presented): A method for transferring a device as claimed in claim 45, wherein the device is a light-emitting device.

Claim 52 (previously presented): A method for transferring a device as claimed in claim 45, wherein the device holding layer includes a surface with a recessed portion shaped to fit the pointed head portion.

Claim 53 (previously presented): A method for transferring a device as claimed in claim 45, wherein the device holding layer is a silicone resin layer.

Claim 54 (new): A method for transferring a device, comprising the steps of:

irradiating, selectively, an interface between a first substrate and a device included on the first substrate with an energy beam and transmitting the energy beam through the first substrate to selectively release the device;

transferring the released device onto a device holding layer included on a device holding substrate;

cleaning the device on the device holding layer after the device is transferred onto the device holding layer; and

transferring the device from the device holding layer onto a second substrate.

Claim 55 (new): A method for transferring a device as claimed in claim 54, further comprising the step of providing an adhesive layer on the second substrate wherein the adhesive layer is irradiated with the energy beam when the device is transferred from the device holding layer onto the second substrate.

Claim 56 (new): A method for transferring a device as claimed in claim 54, wherein the device is formed of a material which produces ablation upon irradiation with the energy beam, and wherein ablation is generated by the selective irradiation with the energy beam to cause exfoliation at an interface between the device and the first substrate.

Claim 57 (new): A method for transferring a device as claimed in claim 56, wherein the material is a nitride semiconductor material.

Claim 58 (new): A method for transferring a device as claimed in claim 57, wherein the nitride semiconductor material is a GaN-based material.

Claim 59 (new): A method for transferring a device as claimed in claim 54, wherein the first substrate is a sapphire substrate.

Claim 60 (new): A method for transferring a device as claimed in claim 54, wherein the device is a light-emitting device.

Claim 61 (new): A method for transferring a device as claimed in claim 54, wherein the device holding layer is a silicone resin layer.

Claim 62 (new): A method for transferring a device, comprising the steps of:

irradiating, selectively, an interface between a first substrate and a device included on the first substrate with an energy beam and transmitting the energy beam through the first substrate to selectively release the device, wherein the device is formed of a nitride semiconductor material which produces ablation upon irradiation with the energy beam, and wherein the ablation is generated by the selective irradiation with the energy beam to cause exfoliation at an interface between the device and the first substrate;

transferring the released device onto a device holding layer included on a device holding substrate; and

transferring the device from the device holding layer onto a second substrate.

Claim 63 (new): A method for transferring a device as claimed in claim 62, further comprising the step of providing an adhesive layer on the second substrate wherein the adhesive layer is irradiated with the energy beam when the device is transferred from the device holding layer onto the second substrate.

Claim 64 (new): A method for transferring a device as claimed in claim 62, wherein the nitride semiconductor material is a GaN-based material.

Claim 65 (new): A method for transferring a device as claimed in claim 62, wherein the first substrate is a sapphire substrate.

Claim 66 (new): A method for transferring a device as claimed in claim 62, wherein the device is a light-emitting device.

Claim 67 (new): A method for transferring a device as claimed in claim 62, wherein the device holding layer is a silicone resin layer.

Claim 68 (new): A method for transferring a device, comprising the steps of:

irradiating, selectively, an interface between a first substrate and a device included on the first substrate with an energy beam and transmitting the energy beam through the first substrate to selectively release the device, wherein the first substrate is a sapphire substrate;

transferring the released device onto a device holding layer included on a device holding substrate; and

transferring the device from the device holding layer onto a second substrate.

Claim 69 (new): A method for transferring a device as claimed in claim 68, further comprising the step of providing an adhesive layer on the second substrate wherein the adhesive layer is irradiated with the energy beam when the device is transferred from the device holding layer onto the second substrate.

Claim 70 (new): A method for transferring a device as claimed in claim 68, wherein the device is formed of a material which produces ablation upon irradiation with the energy beam, and wherein ablation is generated by the selective irradiation with the energy beam to cause exfoliation at an interface between the device and the first substrate.

Claim 71 (new): A method for transferring a device as claimed in claim 70, wherein the material is a nitride semiconductor material.

Claim 72 (new): A method for transferring a device as claimed in claim 71, wherein the nitride semiconductor material is a GaN-based material.

Claim 73 (new): A method for transferring a device as claimed in claim 68, wherein the device is a light-emitting device.

Claim 74 (new): A method for transferring a device as claimed in claim 68, wherein the device holding layer is a silicone resin layer.